

isc N-Channel MOSFET Transistor

IPP60R600E6, IIPP60R600E6

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.6Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

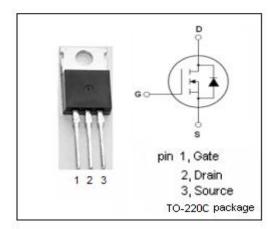
 Provide all benefits of a fast switching super junction MOS while not sacrificing ease of use

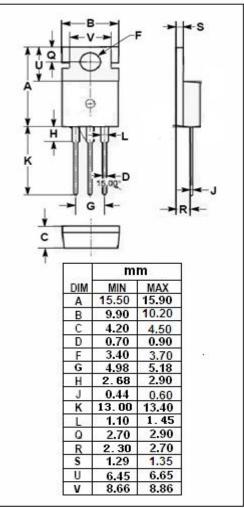
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	600	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	7.3	А	
I _{DM}	Drain Current-Single Pulsed	19	А	
P_D	Total Dissipation @T _C =25℃	63	W	
Tj	Max. Operating Junction Temperature 150		${\mathbb C}$	
T _{stg}	Storage Temperature	-55~150	${\mathbb C}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	2	°C/W	
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C/W	







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =0.2mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; ID=2.4A			0.6	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	I _F =3A; V _{GS} = 0V		0.9		V

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